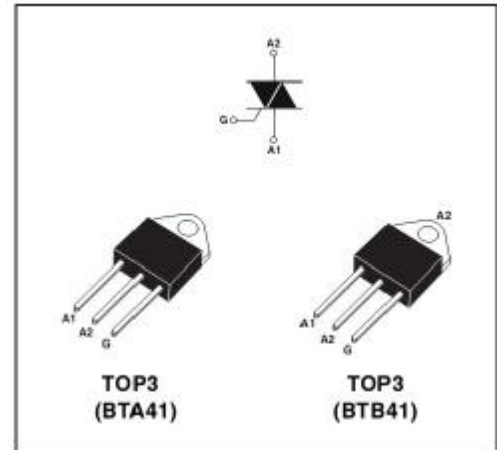


Features:

- NPNPN Bi-direction Triac
- Back multilayer metal electrode
- High temperature reliability
- Glass Passivated junction chipses

Application:

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•Limiting Values

Symbol	Absolute maximum ratings Parameters			Value	Unit
$I_T(RMS)$	RMS on-state current	BTA BTB	$T_c=80^\circ C$ $T_c=90^\circ C$	40	A
I_{TSM}	Non repetitive surge peak on-state current	F=50HZ	t=20ms	410	A
I^2t	I^2t value for fusing	tp=10ms		880	A ² S
di/dt	Critical rate of rise of on-state current		$T_j=125^\circ C$	50	A/us
VDRM/VRRM	Non repetitive surge peak off-state voltage		$T_j=25^\circ C$	1200	V
IGM	Peak gate current	tp=20us	$T_j=125^\circ C$	8	A
PG(AV)	Average gate power dissipation		$T_j=125^\circ C$	1	W
Tstg	Storage junction temperature range			-40to+150	°C
Tj	Operating junction temperature range			-40to+125	

• **Electrical Characteristics(3 quadrant) (Tj=25°C, unless otherwise specified)**

Symbol	Test Condition	Quadrant		Value	Unit
I _{GT}	V _D =12V R _L =100Ω	I II III	MAX	120	mA
V _{GT}			MAX	1.5	V
V _{GD}	T _j =125°C		MIN	0.2	V
I _H	I _T =0.5A		MAX	80	mA
I _L	I _G =1.2I _{GT}		MAX	70	mA
				160	
dv/dt	V _D =2/3V _{DRM} T _j =125°C		MIN	800	V/us
(dv/dt) _c	T _j =125°C		MIN	10	V/us

• **Static Characteristics**

Symbol	Test Conditions			Value	Unit
V _{TM}	I _{TM} = 82A	T _j =25°C	MAX	1.55	V
V _{T0}	Threshold voltage	T _j =125°C	MAX	0.86	V
R _d	Dynamic resistance	T _j =125°C	MAX	6.4	mΩ
I _{DRM} I _{RRM}	V _{DRM} = V _{DRM}	T _j =25°C	MAX	10	uA
		T _j =125°C		2	mA
R _{th(j-c)}	Junction to case (AC)	BTA		0.9	°C/W
		BTB		0.6	

● TO-3P Dimension

